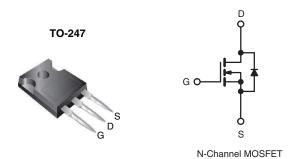
Vishay Siliconix

Power MOSFET



PRODUCT SUMMARY			
V _{DS} (V)	500		
$R_{DS(on)}(\Omega)$	V _{GS} = 10 V	0.40	
Q _g (Max.) (nC)	150		
Q _{gs} (nC)	20		
Q _{gd} (nC)	80		
Configuration	Single		

FEATURES

- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Isolated Central Mounting Hole
- Fast Switching
- · Ease of Paralleling
- Simple Drive Requirements
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-247 package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220 devices. The TO-247 is similar but superior to the earlier TO-218 package because its isolated mounting hole. It also provides greater creepage distances between pins to meet the requirements of most safety specifications.

ORDERING INFORMATION	
Package	TO-247
Lead (Pb)-free	IRFP450PbF

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V _{DS}	500	.,
Gate-Source Voltage			V _{GS}	± 20	V
Continuous Drain Current	V _{GS} at 10 V	$T_C = 25 ^{\circ}C$	L	14	
Continuous Diain Current	V _{GS} at 10 V	T _C = 100 °C	I _D	8.7	Α
Pulsed Drain Current ^a	•		I _{DM}	56	
Linear Derating Factor				1.5	W/°C
Single Pulse Avalanche Energy ^b			E _{AS}	760	mJ
Repetitive Avalanche Current ^a			I _{AR}	8.7	Α
Repetitive Avalanche Energy ^a			E _{AR}	19	mJ
Maximum Power Dissipation	T _C =	25 °C	P_D	190	W
Peak Diode Recovery dV/dtc			dV/dt	3.5	V/ns
Operating Junction and Storage Temperature Range			T _J , T _{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature) for 10 s				300 ^d	
Mounting Torque	6 22 or N	0.00 - 140		10	lbf ⋅ in
Mounting Torque	6-32 or M3 screw			1.1	N⋅m

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b. V_{DD} = 50 V, starting T_J = 25 °C, L = 7.0 mH, R_G = 25 Ω , I_{AS} = 14 A (see fig. 12)
- c. $I_{SD} \leq 14$ A, $dI/dt \leq 130$ A/µs, $V_{DD} \leq V_{DS}, \, T_J \leq 150$ °C
- d. 1.6 mm from case



Vishay Siliconix

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R _{thJA}	-	40	
Case-to-Sink, Flat, Greased Surface	R _{thCS}	0.24	-	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.65	

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		500	-	-	V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	Reference t	to 25 °C, I _D = 1 mA	-	0.63	-	V/°C
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V$	_{GS} , I _D = 250 μA	2.0	-	4.0	V
Gate-Source Leakage	I _{GSS}	V _G	_S = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current		V _{DS} = 5	00 V, V _{GS} = 0 V	-	-	25	
Zero Gate Voltage Drain Gurrent	I _{DSS}	$V_{DS} = 400 \text{ V}, \text{ V}$	/ _{GS} = 0 V, T _J = 125 °C	-	-	250	μΑ
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 8.4 A ^b	-	-	0.40	Ω
Forward Transconductance	9 _{fs}	V _{DS} = 5	0 V, I _D = 8.4 A ^b	9.3	-	-	S
Dynamic							
Input Capacitance	C _{iss}	V	_{GS} = 0 V,	-	2600	-	
Output Capacitance	C _{oss}	V	$_{OS} = 25 \text{ V},$	-	720	-	рF
Reverse Transfer Capacitance	C _{rss}	f = 1.0 l	f = 1.0 MHz, see fig. 5		340	-	1
Total Gate Charge	Q_g			-	-	150	
Gate-Source Charge	Q_{gs}	V _{GS} = 10 V	$V_{GS} = 10 \text{ V}$ $I_{D} = 14 \text{ A}, V_{DS} = 400 \text{ V},$ see fig. 6 and 13 ^b		-	20	nC
Gate-Drain Charge	Q_{gd}	see lig. o and to	-	-	80		
Turn-On Delay Time	t _{d(on)}			-	17	-	
Rise Time	t _r	V _{DD} = 2	50 V, I _D = 14 A,	-	47	-	no
Turn-Off Delay Time	t _{d(off)}	$R_{\rm G} = 6.2 \ \Omega, \ R_{\rm D} = 17 \ \Omega, \ {\rm see \ fig. \ 10^b}$		-	92	-	ns
Fall Time	t _f			-	44	-	
Internal Drain Inductance	L _D	Between lead, 6 mm (0.25") fro	m ,	-	5.0	-	
Internal Source Inductance	L _S	package and center of die contact		-	13	-	nH
Drain-Source Body Diode Characteristic	s				•		
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	14	
Pulsed Diode Forward Current ^a	I _{SM}			-	-	56	A
Body Diode Voltage	V _{SD}	T _J = 25 °C, I	_S = 14 A, V _{GS} = 0 V ^b	-	-	1.4	V
Body Diode Reverse Recovery Time	t _{rr}	T 05.00 I	44.4	-	540	810	ns
Body Diode Reverse Recovery Charge	Q _{rr}	I _J = 25 °C, I _F =	14 A, dl/dt = 100 A/µs ^b	-	4.8	7.2	μC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-			minated b	y L _S and	L _D)

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11) b. Pulse width \leq 300 μs ; duty cycle \leq 2 %



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

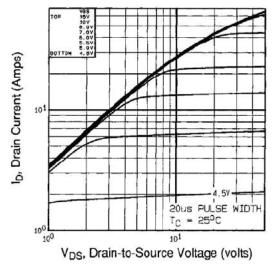


Fig. 1 - Typical Output Characteristics, T_C = 25 °C

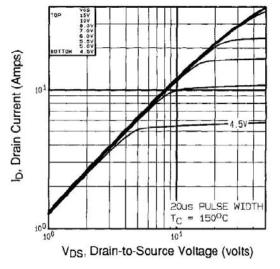


Fig. 2 - Typical Output Characteristics, $T_C = 150$ °C

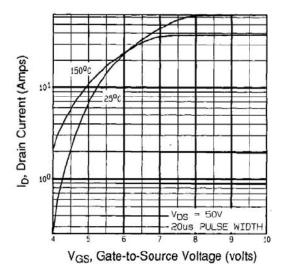


Fig. 3 - Typical Transfer Characteristics

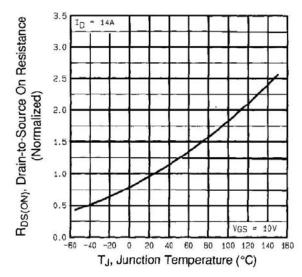


Fig. 4 - Normalized On-Resistance vs. Temperature



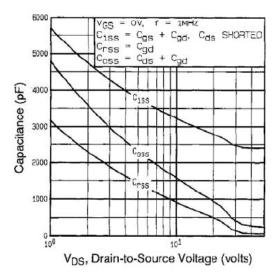


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

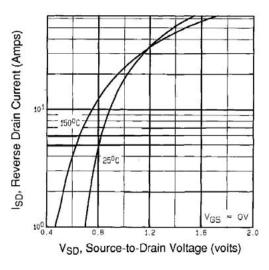


Fig. 7 - Typical Source-Drain Diode Forward Voltage

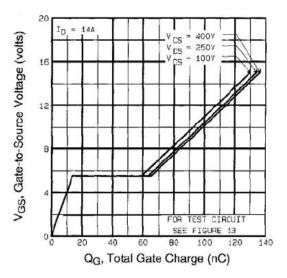


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

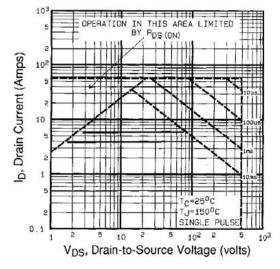


Fig. 8 - Maximum Safe Operating Area



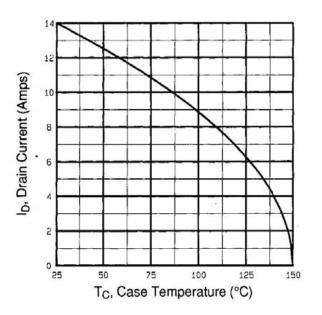


Fig. 9 - Maximum Drain Current vs. Case Temperature

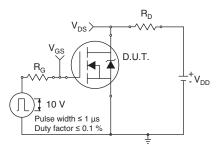


Fig. 10a - Switching Time Test Circuit

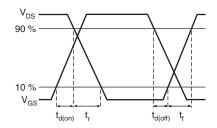


Fig. 10b - Switching Time Waveforms

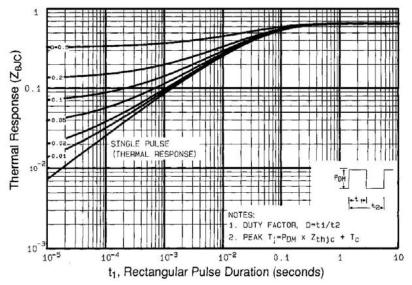


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

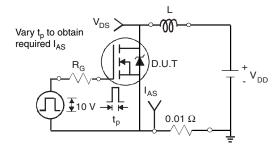


Fig. 12a - Unclamped Inductive Test Circuit

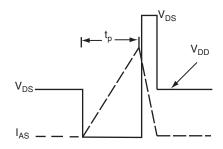


Fig. 12b - Unclamped Inductive Waveforms



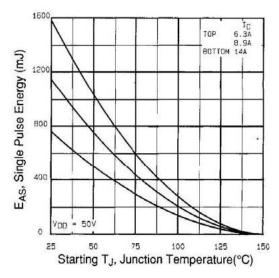


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

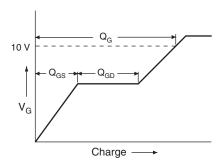


Fig. 13a - Basic Gate Charge Waveform

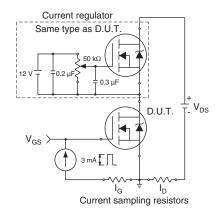
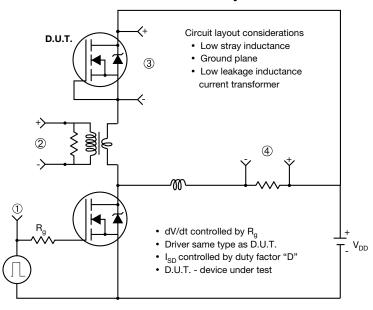


Fig. 13b - Gate Charge Test Circuit



Peak Diode Recovery dV/dt Test Circuit



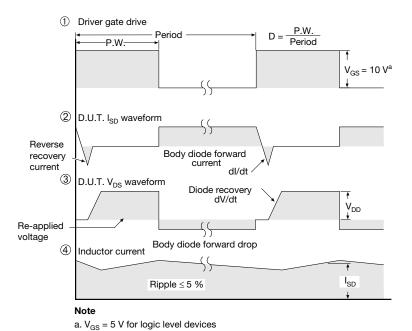


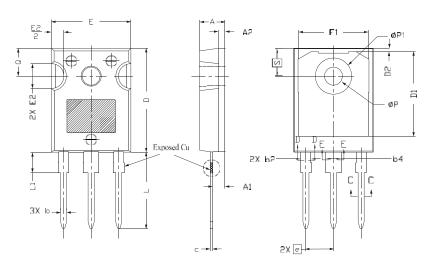
Fig. 14 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91233.



TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9







Section C--C,D-D,E-E

	MILLIMETERS			
DIM.	MIN.	NOM.	MAX.	NOTES
Α	4.83	5.02	5.21	
A1	2.29	2.41	2.55	
A2	1.17	1.27	1.37	
b	1.12	1.20	1.33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
b4	2.87	3.00	3.22	6, 8
b5	2.87	3.00	3.18	
С	0.40	0.50	0.60	6
c1	0.40	0.50	0.56	
D	20.40	20.55	20.70	4

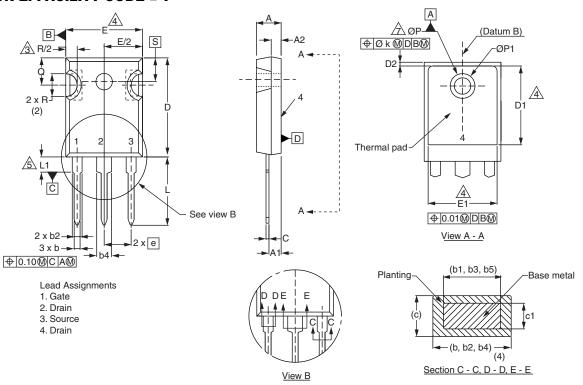
		MILLIMETERS	3	
DIM.	MIN.	NOM.	MAX.	NOTES
D1	16.46	16.76	17.06	5
D2	0.56	0.66	0.76	
Е	15.50	15.70	15.87	4
E1	13.46	14.02	14.16	5
E2	4.52	4.91	5.49	3
е	5.46 BSC			
L	14.90	15.15	15.40	
L1	3.96	4.06	4.16	6
ØΡ	3.56	3.61	3.65	7
Ø P1	7.19 ref.			
Q	5.31	5.50	5.69	
S	5.51 BSC			

- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- $^{(7)}$ Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

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VERSION 2: FACILITY CODE = Y



	MILLIM		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

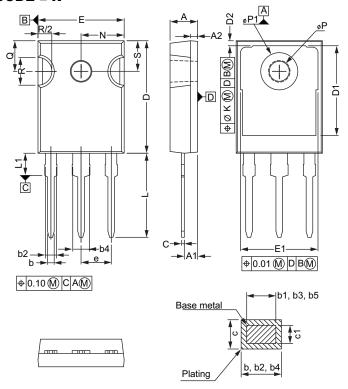
	MILLIN		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
Е	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.2	254	
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

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VERSION 3: FACILITY CODE = N



	MILLIMETERS			
DIM.	MIN.	MAX.		
Α	4.65	5.31		
A1	2.21	2.59		
A2	1.17	1.37		
b	0.99	1.40		
b1	0.99	1.35		
b2	1.65	2.39		
b3	1.65	2.34		
b4	2.59	3.43		
b5	2.59	3.38		
С	0.38	0.89		
c1	0.38	0.84		
D	19.71	20.70		
D1	13.08	-		

	MILLIMETERS		
DIM.	MIN.	MAX.	
D2	0.51	1.35	
E	15.29	15.87	
E1	13.46	1	
е	5.46 BSC		
k	0.254		
L	14.20	16.10	
L1	3.71	4.29	
N	7.62	BSC	
Р	3.56	3.66	
P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

ECN: E22-0452-Rev. G, 31-Oct-2022

DWG: 5971

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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Vishay

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